arXiv:quant-ph/0410150v1 20 Oct 2004

Universal quantum computation with electron spins in quantum dots based on superpositions of space-time paths and Coulomb blockade

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Abstract

Using electrostatic gates to control the electron positions, we present a new controlled-NOT gate based on quantum dots. The qubit states are chosen to be the spin states of an excess conductor electron in the quantum dot; and the main ingredients of our scheme are the superpositions of space-time paths of electrons and the effect of Coulomb blockade. All operations are performed only on individual quantum dots and are based on fundamental interactions. Without resorting to spin-spin terms or other assumed interactions, the scheme can be realized with a dedicated circuit and a necessary number of quantum dots. Gate fidelity of the quantum computation is also presented.

PACS numbers: 03.67.Lx; 73.61.-b

Keywords: Quantum computation; Semiconductor quantum dot

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I. INTRODUCTION

The study of quantum computing and quantum information processing has received great attentions in the past decade[1]. Among several proposals of implementing quantum information processing in realistic physical systems, solid state quantum computing is one of the most promising candidates for future quantum computer architecture due to its scalability. Meanwhile, the idea of using spin degree of freedom in electronics[2] has been strongly supported from recent experiments showing unusually long spin decoherence time in semiconductors. The first QC scheme based on electron spin in semiconductor QD was proposed by Loss and Divincenzo[3], in which the controlling operations are effected by gating of the tunnelling barrier between neighboring dots, and one-qubit operations by applied magnetic field. Kane designed a silicon based nuclear spin quantum computer[4], information is encoded into the nuclear spins of donor atoms in doped silicon electronic devices. Local operations on individual spins are performed using externally applied electric fields, and interaction between qubits is mediated through the donor-electron exchange interaction. In Ref. [5], optical RKKY interaction between charged semiconductor QDs is generated via virtual excitation of delocalized excitons, and it provides an efficient coherent control of the spins. Very recently, Calarco et al.[6] presented an all optical implementations of QC with semiconductor QDs, where two-qubit gates are realized by switching on trion-trion coulomb interactions between different QDs, state selectivity is achieved via conditional laser excitation exploring Pauli exclusion principle.

The idea of most existing QC schemes is to design an effective Hamiltonian and then find or adjust a physical system to evolve approximately under the effective Hamiltonian. Any deviation from the "beautiful" effective Hamiltonian in practical physics system will bring complexity, even disaster, to the practical QC[7]. In this paper, we give a new QC scheme based on a more fundamental Hamiltonian in solid state physics. The qubit states are selected as the spin states of an excess electron stored in a semiconductor QD. The Hamiltonian of electrons in semiconductor QDs dressed by an external magnetic field can be described as following

$$\begin{aligned} H &= \sum_i h_i, \\ h_i &= \frac{1}{2m_e^*} P_i^2 - g\mu_B \mathbf{B_i} \cdot \mathbf{S_i} + V(r_i). \end{aligned} \tag{1}$$

where single-particle Hamiltonian h_i describes the electron dynamics confined to semiconductor QD. m_e^* is the effective mass of electron in semiconductor QD. We allow for a local magnetic field $\mathbf{B_i}$ applied on QD i. $V(r_i)$ is the confinement-potential experienced by the electron in QD.

All operations in our scheme are performed on individual QDs. Using single-qubit rotation and adjusting gate voltage to drive electron between QDs through one dimensional quantum wire, a quantum control gate can be realized naturally. The detailed descriptions on design of a CNOT gate are given in Sec. II. Physical implementation and a brief discussion on gate fidelity are presented in Sec. III. Our conclusions are summarized in Sec. IV.

II. FORMULA FOR QUANTUM GATE

It is well known that single qubit and CNOT gates together can be used to implement an arbitrary unitary operation, and therefore are universal for quantum computation[1]. A single qubit is a vector $|\psi\rangle = a|0\rangle + b|1\rangle$ parameterized by two complex numbers satisfying $|a|^2 + |b|^2 = 1$. Operations on a qubit must preserve this norm, and thus are described by 2×2 unitary matrices. Any single qubit rotations can be realized by two of the following three rotation operators $R_x(\theta) = e^{-i\theta\sigma_x}$, $R_y(\theta) = e^{-i\theta\sigma_y}$, and $R_z(\theta) = e^{-i\theta\sigma_z}$, where σ_x, σ_y, and σ_z are Pauli matrices.

In textbook, a CNOT operator is described by a 4×4 matrix,

$$CNOT = \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 0 & 1 \\ 0 & 0 & 1 & 0 \end{pmatrix}, \tag{2}$$

it can be rewritten as

$$CNOT = \frac{1}{2}[I \otimes \sigma_x - \sigma_z \otimes \sigma_x + I \otimes I + \sigma_z \otimes I], \tag{3}$$

where I is 2×2 identity matrix. Further, substituting Eq. (3) into $CNOT = -ie^{i\frac{\pi}{2}CNOT}$,

we have

$$
\begin{aligned}
CNOT &= e^{-i\frac{\pi}{2}I\otimes I}\cdot e^{i\frac{\pi}{4}(I\otimes\sigma_x-\sigma_z\otimes\sigma_x+I\otimes I+\sigma_z\otimes I)},\\
&= e^{-i\frac{\pi}{4}I\otimes I}\cdot e^{i\frac{\pi}{4}I\otimes\sigma_x}\cdot e^{i\frac{\pi}{4}\sigma_z\otimes I}\cdot e^{-i\frac{\pi}{4}\sigma_z\otimes\sigma_x},\\
&= e^{-i\frac{\pi}{4}I\otimes I}\cdot e^{i\frac{\pi}{4}I\otimes\sigma_x}\cdot e^{i\frac{\pi}{4}\sigma_z\otimes I}\cdot\frac{1}{\sqrt{2}}(I\otimes I-i\sigma_z\otimes\sigma_x),\\
&= e^{-i\frac{\pi}{4}I\otimes I}\cdot e^{i\frac{\pi}{4}I\otimes\sigma_x}\cdot e^{i\frac{\pi}{4}\sigma_z\otimes I}\cdot\frac{1}{\sqrt{2}}[I\otimes I-i(\sigma_z\otimes I)\cdot(I\otimes\sigma_x)],\\
&= e^{-i\frac{\pi}{4}I\otimes I}\cdot e^{i\frac{\pi}{4}I\otimes\sigma_x}\cdot e^{i\frac{\pi}{4}\sigma_z\otimes I}\cdot\frac{1}{\sqrt{2}}(I\otimes I+e^{-i\frac{\pi}{2}}\cdot e^{-i\frac{3\pi}{2}\sigma_z\otimes I}\cdot e^{-i\frac{\pi}{2}I\otimes\sigma_x}).
\end{aligned}
\tag{4}
$$

The first term at the last line of Eq. (4) can easily be realized by letting two qubits evolve freely under each single electron Hamiltonian respectively without any operations. The second and the third terms are only single spin rotations. By the superposition of electron spin state and charge position, the fourth term in Eq. (4) can be implemented naturally, which will be illustrated in Sec. III. So, only six steps(including five operations) are required to complement a CNOT quantum gate given by Eq. (4). Compared with the CNOT gate presented in ref. [3], there is no need for spin swap operation in our scheme, and operations are performed on individual QDs here. Furthermore, four terms on the right side of Eq. (4) commute each other, we can exchange the operator sequence arbitrarily.

III. PHYSICAL IMPLEMENTATION

The spin states of the excess conductor electron of QD are employed as qubits. Manipulating a single spin can be done by applying a pulsed local magnetic field, two-qubit control gate in this paper is realized by a specific spacial distribution of QDs. The architecture of our designed CNOT gate is shown in Fig. 1, where the gray thick lines stand for one-dimension quantum wires, which are used to coherently transport electrons between QDs[9]. Eight QDs are needed to implement a CNOT gate. Initial states of two qubits(control qubit and target qubit) are stored in spin states of the excess electron in QD X_1 and X_2 respectively, and final states of the two qubits are defined as the spin states of electron in QDs $Y_1$and Y_2. QDs w_1, w_2, w_3, w_4, Y_1, and Y_2 are all empty of electrons in the initial time. Firstly, the electron is being driven from QD X_1 to QD w_1 and w_2 by adjusting gate voltage. The design of electric gates can refer to the principle of single electron tunnelling(SET) transistor[8] and the flying qubit in one-dimensional quantum wires[9]. Assuming the two paths and two QDs

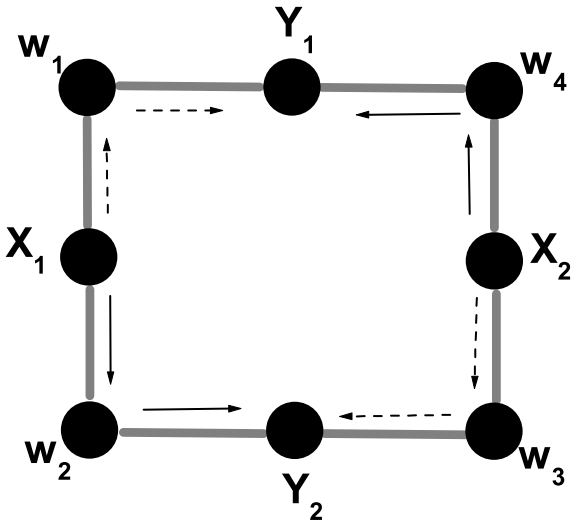

FIG. 1: Architecture for implementing a CNOT gate. Black spheres stand for quantum dots, and gray lines stand for one dimensional quantum wires.

(w_1 and w_2)are symmetric, the probabilities of electron in QD w_1 and w_2 will be equal in theory. By the same method, The electron in QD X_2 is also being driven into QD w_3 and w_4 in parallel. Secondly, we apply an external local magnetic field along z direction on QD w_1 to do a spin rotation $e^{-i\frac{3\pi}{2}\sigma_z}$. Thirdly, an external local magnetic field along x direction on QD w_4 is used to complement operator $e^{-i\frac{\pi}{2}\sigma_x}$. Fourthly, apply two electric fields on QD w_1 and QD w_4 respectively to create a global phase difference $e^{-i\frac{\pi}{2}}$ between QDs w_1, w_4 and QDs w_2, w_3. At last, two electrons are pushed from QDs w_1, w_4 to QD Y_1, and from QDs w_2 and w_3 to QD Y_2 respectively. Adjusting gate voltage to eliminate the case that two electrons site on QD Y_1 or Y_2 simultaneously. According to the coulomb blockade effect, there are only two possible pathes for the two electrons actually occur. One is $X_1 \rightarrow w_2 \rightarrow Y_2$; $X_2 \rightarrow w_4 \rightarrow Y_1$(Solid arrows in Fig. 1), The other is $X_1 \rightarrow w_1 \rightarrow Y_1$; $X_2 \rightarrow w_3 \rightarrow Y_2$(Dashed arrows). In mathematic language, the above process can be described as following,

$$|S_{X_1}\rangle \otimes |S_{X_2}\rangle = [\rho_{w_1} e^{-i\frac{\pi}{2}} e^{-i\frac{3\pi}{2}\sigma_z} |S_{X_1}\rangle + \rho_{w_2}|S_{X_1}\rangle] \bigotimes [\rho_{w_3} e^{-i\frac{\pi}{2}} e^{-i\frac{\pi}{2}\sigma_x} |S_{X_2}\rangle + \rho_{w_4}|S_{X_2}\rangle], \quad (5)$$

where ρ_{w_1} and ρ_{w_2} are the probabilities of electron in QD w_1 and QD w_2 respectively, ρ_{w_3} and ρ_{w_4} are the probabilities of electron in QD w_3 and QD w_4 respectively. Further, we expand Eq. (5) by summation of possible pathes mentioned above, only two terms are retained,

$$\begin{aligned} |S_{X_1}\rangle \otimes |S_{X_2}\rangle &= [\rho_{w_1}\rho_{w_3} e^{i\frac{\pi}{2}} e^{-i\frac{3\pi}{2}\sigma_z \otimes I} \cdot e^{-i\frac{\pi}{2} I \otimes \sigma_x} |S_{X_1}\rangle \otimes |S_{X_2}\rangle + \rho_{w_2}\rho_{w_4} I \bigotimes I |S_{X_1}\rangle \otimes |S_{X_2}\rangle], \\ &= [\rho_{w_1}\rho_{w_3} e^{i\frac{\pi}{2}} e^{-i\frac{3\pi}{2}\sigma_z \otimes I} \cdot e^{-i\frac{\pi}{2} I \otimes \sigma_x} + \rho_{w_2}\rho_{w_4} I \bigotimes I] |S_{X_1}\rangle \otimes |S_{X_2}\rangle. \quad (6) \end{aligned}$$

We can see that the fourth term in Eq. (4) can be complemented by the above architecture under the condition of equal probabilities($\rho_{w_1} = \rho_{w_2} = \rho_{w_3} = \rho_{w_4}$). Two single-qubit operations (the 2nd and 3rd terms in Eq. (4))can be performed by applied two local pulsed magnetic fields along X and Z directions on QDs X_1 and X_2 respectively at the initial time. They can also be performed on QDs Y_1 and Y_2 at the final time. The successful criterium of the above control gate is that two electrons must arrive at QDs Y_1 and Y_2 at the final time. If QDs Y_1 and Y_2 only process one electron at the final time(50% probability), then the control operation will be discarded. So, a measurement must be done at the final time to check whether the control gate has been performed successfully.

If a two-qubit control gate has been done successfully, the potential quantum error of our scheme comes from the asymmetric probabilities of electron positions, namely, $\rho_{w_1} \neq \rho_{w_2}$, $\rho_{w_3} \neq \rho_{w_4}$. We define the fidelity of our CNOT gate induced by the asymmetric probabilities of electron positions as

$$F = \begin{cases} 2 - U^{\dagger}U^{'}, & U^{\dagger}U^{'} \geq 1; \\ U^{\dagger}U^{'}, & U^{\dagger}U^{'} < 1, \end{cases} \tag{7}$$

and

$$U^{\dagger}U^{'} = \frac{\rho_{w_1}\rho_{w_3}\rho^{\prime}_{w_1}(x)\rho^{\prime}_{w_3}(x') + \rho_{w_2}\rho_{w_4}\rho^{\prime}_{w_2}(1-x)\rho^{\prime}_{w_4}(1-x')}{(\rho_{w_1}\rho_{w_3})^2 + (\rho_{w_2}\rho_{w_4})^2}, \tag{8}$$

$$\rho^{\prime}(x) = x, \tag{9}$$

where operator U is the ideal CNOT operator described by Eq. (6), U' is the practical operator with the consideration of potential asymmetric probabilities of electron positions in real space. under the case of equal probabilities (symmetric case), we have $\rho^{'}_{w_i} = \rho_{w_i} = 0.5$, and the fidelity is equal to 1 by the definition of Eq. (7). we use $x(0 \leq x \leq 1)$to measure the magnitude of asymmetry of electron positions, and the symmetric case corresponds to $x = 0.5$. Fidelity of the CNOT gate as a function of the asymmetry in case $x = x'$ is plotted in Fig. 2. It is shown, in Fig. 2, that fidelity will be up 99% when the asymmetry does not exceed 10%.

Under the precondition of high fidelity, a small size difference between QD w_1 and w_2(and between QD w_3 and w_4) is permitted. Reminding that QDs w_1 and w_4 does not need the same in size. As a result, the single-qubit operations can be performed selectively with different frequencies, and the local pulsed magnetic field may also be replaced by optical

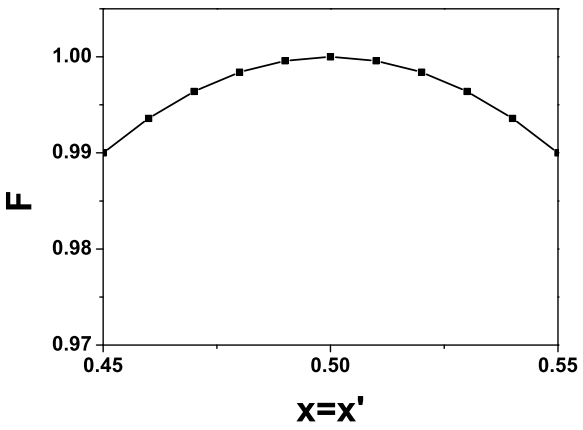

FIG. 2: The fidelity of the CNOT gate as a function of the asymmetry of electron positions

operations, and the single qubit rotations can be proceeded by applying two laser fields which exactly satisfy the Raman-resonance condition between spin-up state and spin-down state[10][11]. Optical operation will sufficiently reduce single-qubit operation time.

Operation time and decoherence time are critical criteria on the feasibility of a QC scheme[1]. For a single spin flip rotation, a switching time of $\tau_s = 30ps$ is required, using a magnetic field of $B = 1T$[12]. Considering the switching on/off time of electric field is about $20 \sim 30ps$, gate voltage must be adjusted carefully to create a small potential difference between QDs w_1, w_4, and QDs w_2, w_3[13]. If two pulsed lasers are used to complement a single qubit operation, the single spin flip operation time is about ten picoseconds for a given coupling constant between Laser and QD $\Omega = 1meV$. Decoherence time of spin states in semiconductor QD has also been extensively studied in theory and experiment[14][15], and coherent transport of spin charge in semiconductor has been discussed in detail. [2][9][12]. State initialization and read-out can be implemented using spin filters and polarizers in any designs[12][16]. Our motivation is to show a new theoretical design direction on quantum control gate based on semiconductor QDs. So, we do not focus more attentions on challenges common to all other implementations in electron spins and QDs system. The great challenge to our scheme, which is different from other schemes in practical, is how to manipulate single electron transport coherently between QDs through one-dimensional quantum wire or nanotube, this difficulty can be solved by the rapid development of single electron tunnelling transistor technologies.

IV. CONCLUDING REMARKS

In summary, we have presented a new QC scheme based on semiconductor QDs system. The superposition of spin state and charge position in real space and coulomb blockade effect are introduced to design a CNOT gate. All the quantum states' evolutions in our scheme base on a more fundamental Hamiltonian. No direct spin-spin coupling is needed here. Our scheme, which is based on solid state QD, is essentially different from the mobile qubit scheme[9], and spin state operations are more stable in general. As we know, it is the first time that a control gate is designed by the superposition of electron spin state and charge position in quantum computation based on QDs system. Our scheme is simple except for a dedicated circuit and more QDs needed. Furthermore, our scheme can safely be extended into the charge qubit case by replacing each QD with a coupled QDs, and qubit states are defined as the excess electron charge states in coupled QDs.

Acknowledgments

This work was partially supported by the National Science Council of ROC under Contract No. NSC-93-2120-M-006-005, No. NSC-93-2112-M-006-011, No. NSC-93-2112-M-006-019 and National Center for Theoretical Science(South), Taiwan.

[1] M. A. Nielsen, and I. L. Chuang, *Quantum Computation and Quantum Information*, (Cambridge University Press, 2000).

[2] D. D. Awschalom, D. Loss, and N. Samarth, *Semiconductor Spintronics and Quantum Computation*, (Springer-Verlag Berlin Heidelberg, 2002).

[3] D. Loss, and D. P. DiVincenzo, *Phys. Rev. A* **57**, 120 (1998).

[4] B. E. Kane, *Nature* **393**, 133(1998).

[5] C. Piermarocchi, Pochung Chen, L. J. Sham, and D. G. Steel, *Phys. Rev. Lett.* **89**, 167402(2002).

[6] T. Calarco, A. Datta, P. Fedichev, E. Pazy, and P. Zoller, *Phys. Rev. A* **68**, 012310(2003).

[7] Xuedong Hu, and S. Das Sarma, *Phys. Stat. Sol(b)* **238**, 360(2003); Xuedong Hu, and S. Das Sarma, *Phys. Rev. A* **68**, 052310(2003).

[8] H. Grabert, and M. H. Devoret, *Single charge tunneling:coulomb blockade phenomena in nanostructures*, (Plenum Press, New York, 1992); Y. T. Tan, T. Kamiya, Z. A. K. Durrani, and H. Ahmed, *J. Appl. Phys.* **94**, 633(2003).

[9] A. E. Popescu, and R. Ionicioiu, *Phys. Rev. B* **69**, 245422(2004);
C. H. W. Barnes, J. M. Shilton, and A. M. Robinson, *Phys. Rev. B* **62**, 8410(2000).

[10] Nikolay V Vitanov, Thomas Halfmann, Bruce W Shore, and Klaas Bergmann, *Annu. Rev. Phys. Chem.* **52**, 763(2001).

[11] A. Imamoglu, D. D. Awschalom, G. Burkard, D. P. DiVincenzo, D. Loss, M. Sherwin, and A. Small, *Phys. Rev. Lett.* **83**, 4204(1999).

[12] Hans-Andreas Engel, Patrik Recher, Daniel Loss, *Solid State communications* **119**, 229(2001).

[13] S. Bednarek, B. Szafran, K. Lis, and J. Adamowski, *Phys. Rev. B* **68**, 155333(2003).

[14] Rogerio de Sousa, and S. Das Sarma, *Phys. Rev. B* **67**, 033301(2003).

[15] B. Beschoten, E. Johnston-halperin, D. K. Young, M. Poggio, J. E. Grimaldi, S.Keller, S. P. DenBaars, U. K. Mishra, E. L. Hu, and D. D. Awschalom, *Phys. Rev. B* **63**, 121202(R)(2001).

[16] R. Ioniicioiu, and I. D'Amico, *Phys. Rev. B* **67**, 041307(R)(2003).